

## REMARKS

A typographical error in claim 20 has been corrected. Since this simply corrects a matter of form, it should be enterable as a matter of right.

In the renewed final rejection, the Examiner suggests that the Applicants do not dispute that the germanium concentration in Liu's region is different. The point that Applicants were trying to make was that since Liu is an amorphous region, concentration has no meaning. Concentration can have no effect in the amorphous or totally disordered structure. The structure is damaged and, therefore, whatever impurities are provided at whatever concentration would not necessarily have any effect that they would have in a non-amorphous region. In other words, there is no reason to conclude from the fact that certain things happen in non-amorphous crystal structures that the same things would happen in amorphous crystal structures.

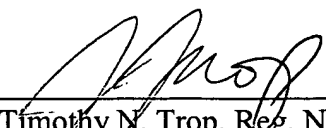
Therefore, an argument of inherency cannot lie. Moreover, since the reference does not talk about any type of strained junction, it is hard to believe that one is formed.

In point of fact, it is hard to even imagine talking about a junction in an amorphous semiconductor. Because it is amorphous, it is resistive and disordered. Therefore, there can be no junction, there can be no source drain, and it makes no sense to talk about a strained junction.

In view of these remarks, reconsideration is respectfully requested.

Respectfully submitted,

Date: September 17, 2004



---

Timothy M. Trop, Reg. No. 28,994  
TROP, PRUNER & HU, P.C.  
8554 Katy Freeway, Ste. 100  
Houston, TX 77024  
713/468-8880 [Phone]  
713/468-8883 [Fax]